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42. The device of claim 40 wherein said ridge is less than about 200Å measured by AFM.

43. The device of claim 40 wherein said crystalline semiconductor layer comprising silicon is formed by plasma CVD or LPCVD and crystallization conducted after said plasma CVD or LPCVD.

44. The device of claim 40 wherein the silicon oxide of said insulating layer is formed by wet oxidation or hydrogen chloride oxidation.

REMARKS

Entry of these claims prior to further examination is requested.

Applicants also call attention to the enclosed document listed on the attached form PTO-1449. No translation of the document beyond the brief abstract provided herein, is readily available to applicants.

PATENT
ATTORNEY DOCKET NO. 07977/093002/US3164D1

If there are any charges, or any credits, please apply them to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 9/27/99



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